NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Tr1 and Tr2
V_{CEO}	50V
I _C	100mA
R_1	10kΩ

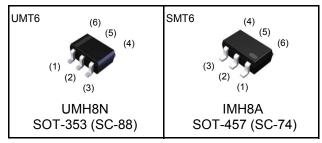
Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC114T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

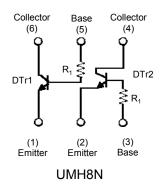
Application

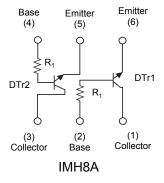
Inverter circuit, Interface circuit, Driver circuit

Outline



•Inner circuit





Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
UMH8N	UMT6	2021	TN	180	8	3,000	H8
IMH8A	SMT6	2928	T110	180	8	3,000	H8

● Absolute maximum ratings (Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage		V _{CEO} 50		V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I _C *1	100	mA
Collector Power dissipation UMH8N IMH8A		P _D *2	150 (Total) ^{*3}	mW
		гЪ	300 (Total)*4	mW
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

●Electrical characteristics(Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μА
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 10mA / 1mA	-	-	0.3	V
DC current gain	h _{FE}	V_{CE} = 5V , I_{C} = 1mA	100	250	600	-
Input resistance	R ₁	-	7	10	13	kΩ
Transition frequency	f _T *1	V _{CE} = 10V, I _E = -5mA f = 100MHz	-	250	-	MHz

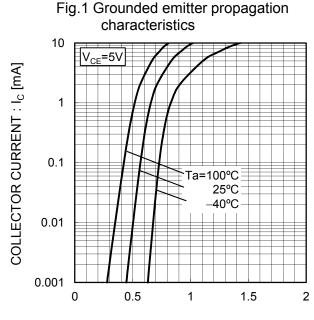
^{*1} Characteristics of built-in transistor

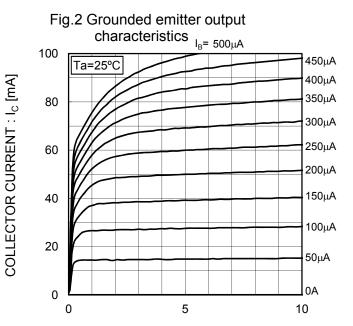
^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

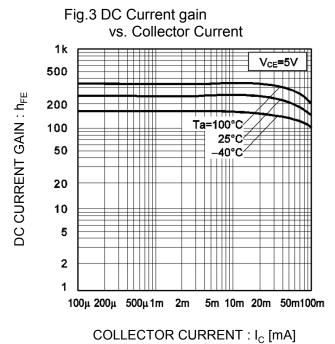
^{*4 200}mW per element must not be exceeded.

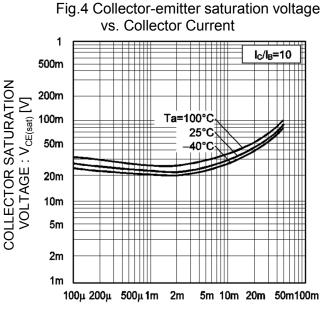
●Electrical characteristic curves (Ta = 25°C) <For DTr1 and DTr2 in common>





BASE TO EMITTER VOLTAGE : $V_{\text{BE}}[V]$ COLLECTOR TO EMITTER VOLTAGE : $V_{\text{CE}}[V]$

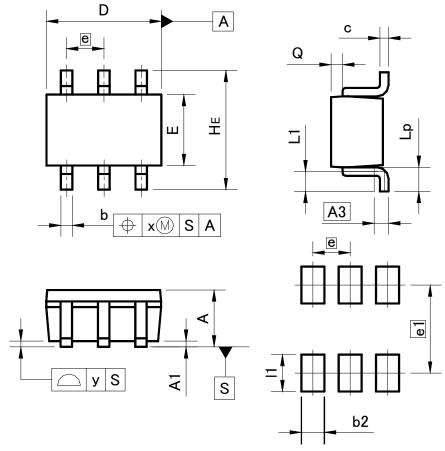




COLLECTOR CURRENT : I_C [mA]

●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

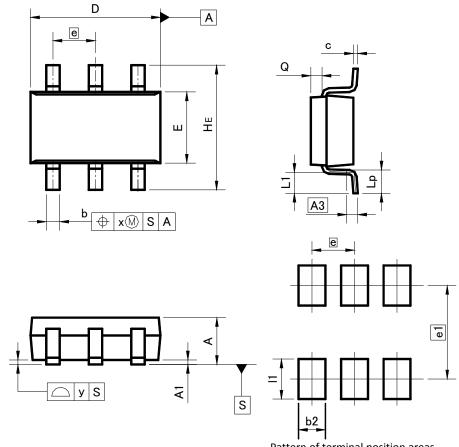
DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.:	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.	65	0.0	26
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
Х	_	0.10		0.004
У	_	0.10	_	0.004

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.40	-	0.016	
e1	1.5	1.55		061	
I1	_	0.65	_	0.026	

Dimension in mm / inches

●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.5	25	0.0	10
b	0.25	0.40	0.010	0.016
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
Е	1.50	1.80	0.059	0.071
е	0.9	95	0.0	37
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20		0.008
У	_	0.10	_	0.004

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
b2		0.60	_	0.024
e1	2.	10 0.083		083
l1	_	0.90	_	0.035

Dimension in mm / inches

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